



RF MOSFET Power Transistor, 2W, 28V

500 - 1000 MHz

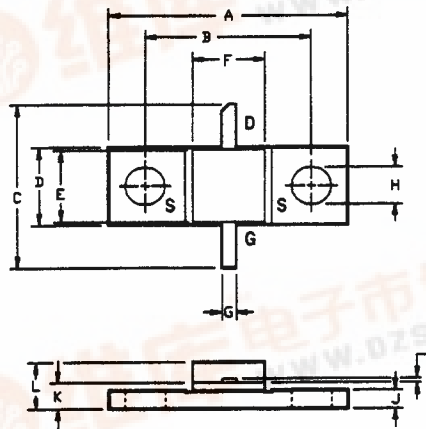
LF2802A

V2.00

Features

- N-Channel Enhancement Mode Device
- DMOS Structure
- Lower Capacitances for Broadband Operation
- Common Source Configuration
- Lower Noise Floor
- Applications

Broadband Linear Operation
500 MHz to 1400 MHz



Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	65	V
Gate-Source Voltage	V_{GS}	20	V
Drain-Source Current	I_{DS}	0.7	A
Power Dissipation	P_D	8	W
Junction Temperature	T_J	200	°C
Storage Temperature	T_{STG}	-55 to +150	°C
Thermal Resistance	θ_{JC}	21.8	°C/W

LETTER DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	20.70	20.96	.815	.825
B	14.35	14.61	.565	.575
C	13.72	14.22	.540	.560
D	6.27	6.53	.247	.257
E	6.22	6.48	.245	.255
F	6.22	6.48	.245	.255
G	1.14	1.40	.045	.055
H	2.92	3.18	.115	.125
J	1.40	1.65	.055	.065
K	1.96	2.46	.077	.097
L	3.61	4.37	.142	.172
M	.08	.15	.003	.006

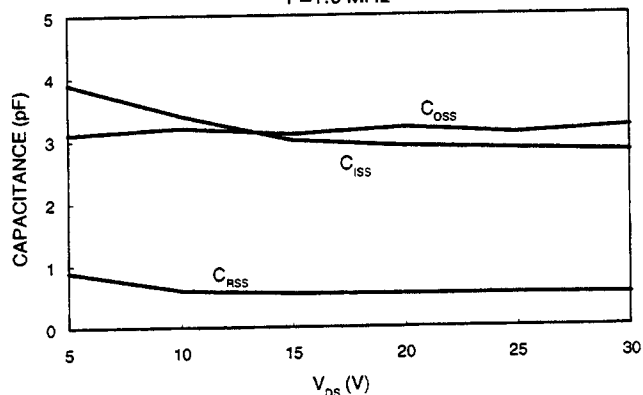
Electrical Characteristics at 25°C

Parameter	Symbol	Min	Max	Units	Test Conditions
Drain-Source Breakdown Voltage	BV_{DSS}	65	-	V	$V_{GS}=0.0\text{ V}$, $I_{DS}=1.0\text{ mA}$
Drain-Source Leakage Current	I_{DSS}	-	0.5	mA	$V_{DS}=28.0\text{ V}$, $V_{GS}=0.0\text{ V}$
Gate-Source Leakage Current	I_{GSS}	-	0.5	μA	$V_{GS}=20\text{ V}$, $V_{DS}=0.0\text{ V}$
Gate Threshold Voltage	$V_{GS(TH)}$	2.0	6.0	V	$V_{DS}=10.0\text{ V}$, $I_{DS}=5.0\text{ mA}$
Forward Transconductance	G_M	40	-	mS	$V_{DS}=10.0\text{ V}$, $I_{DS}=50.0\text{ mA}$, $\Delta V_{GS}=1.0\text{ V}$, 80 μs Pulse
Input Capacitance	C_{ISS}	-	3.5	pF	$V_{DS}=28.0\text{ V}$, $F=1.0\text{ MHz}$
Output Capacitance	C_{OSS}	-	3.75	pF	$V_{DS}=28.0\text{ V}$, $F=1.0\text{ MHz}$
Reverse Capacitance	C_{RSS}	-	1.2	pF	$V_{DS}=28.0\text{ V}$, $F=1.0\text{ MHz}$
Power Gain	G_P	10	-	dB	$V_{DS}=28.0\text{ V}$, $I_{DQ}=25\text{ mA}$, $P_{OUT}=2.0\text{ W}$, $F=1.0\text{ GHz}$
Drain Efficiency	η_D	40	-	%	$V_{DS}=28.0\text{ V}$, $I_{DQ}=25\text{ mA}$, $P_{OUT}=2.0\text{ W}$, $F=1.0\text{ GHz}$
Load Mismatch Tolerance	VSWR-T	-	20:1	-	$V_{DS}=28.0\text{ V}$, $I_{DQ}=25\text{ mA}$, $P_{OUT}=2.0\text{ W}$, $F=1.0\text{ GHz}$

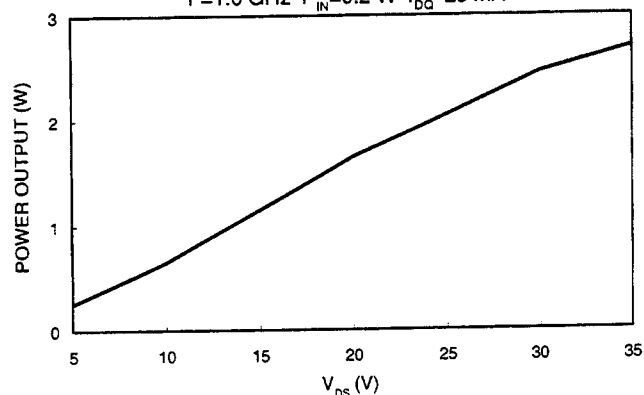
Typical Broadband Performance Curves

CAPACITANCES vs VOLTAGE

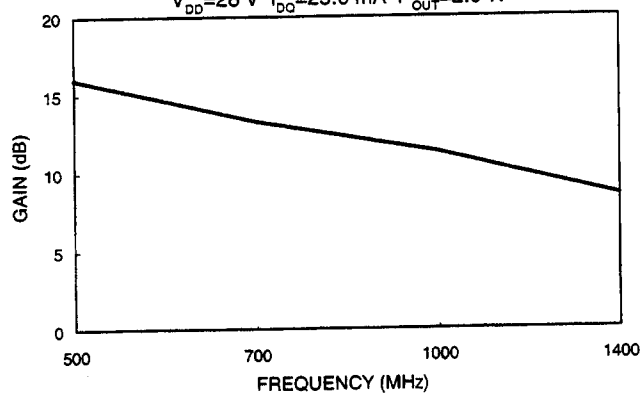
F=1.0 MHz



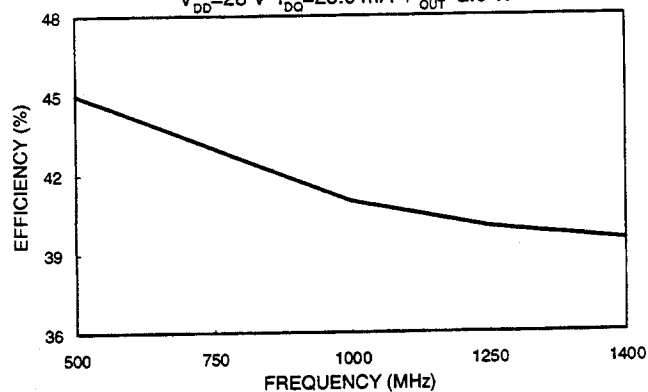
POWER OUTPUT vs VOLTAGE

F=1.0 GHz $P_{IN}=0.2$ W $I_{DG}=25$ mA

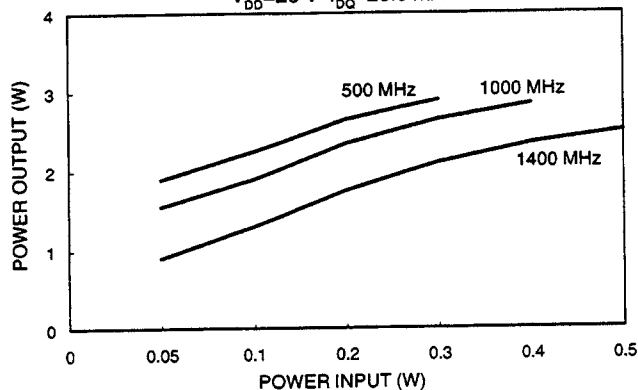
GAIN vs FREQUENCY

 $V_{DD}=28$ V $I_{DG}=25.0$ mA $P_{OUT}=2.0$ W

EFFICIENCY vs FREQUENCY

 $V_{DD}=28$ V $I_{DG}=25.0$ mA $P_{OUT}=2.0$ W

POWER OUTPUT vs POWER OUTPUT

 $V_{DD}=28$ V $I_{DG}=25.0$ mA

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Specifications Subject to Change Without Notice.

Typical Device Impedance

Frequency (MHz)	Z_{IN} (OHMS)	Z_{LOAD} (OHMS)
500	$10.0 - j 41.5$	$40.0 + j 53.0$
1000	$4.2 - j 12.0$	$11.85 + j 33.0$
1400	$3.5 - j 1.0$	$7.5 + j 23.3$

$V_{DD}=28\text{ V}$, $I_{DQ}=25\text{ mA}$, $P_{OUT}=2.0\text{ Watts}$

Z_{IN} is the series equivalent input impedance of the device from gate to source.
 Z_{LOAD} is the optimum series equivalent load impedance as measured from drain to ground.

RF Test Fixture

